

UV-B Sensor

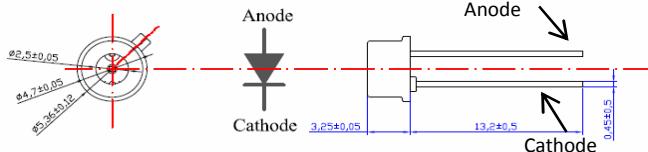
GUVB-T11GD-L

Features	Aluminium Gallium Nitride Based Material Schottky-type Photodiode Photovoltaic Mode Operation Good Visible Blindness High Responsivity & Low Dark Current
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Applications UV-B Lamp Monitoring
UV-B LED Monitoring

Outline Diagrams and Dimensions



Absolute Maximum Ratings

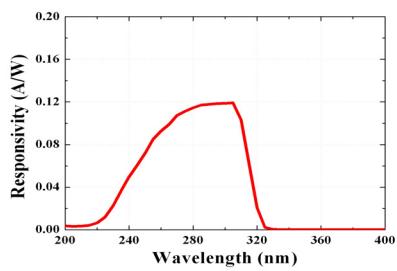
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T _{st}	-40	90	°C	
Operating Temperature	T _{op}	-30	85	°C	
Reverse Voltage	V _{r, max.}		3	V	
Forward Current	I _{f,max.}		1	mA	
Optical Source Power Range	P _{opt}	0.01μ	100m	W/cm ²	UVB Lamp
Soldering Temperature	T _{sol}		260	°C	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100mW/cm²

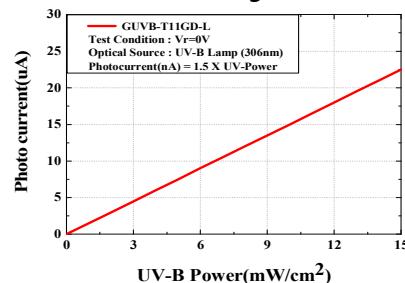
Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			20	nA	$V_r = 0.1 \text{ V}$
Photo Current	I_{ph}	1.35	1.5	1.65	μA	UVB Lamp, 1mW/cm^2
Temperature Coefficient	I_{tc}		0.1		$^\circ\text{C}$	UVB Lamp
Responsivity	R		0.13		A/W	$\lambda = 300 \text{ nm}, V_r = 0 \text{ V}$
Spectral Detection Range	λ	220		320	nm	10% of R
Active area			1.536		mm^2	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD. Insulate the cap of TO-CAN or it can cause malfunction of the device.